

RB481K

Diodes

Schottky Barrier Diode

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●Applications

Low current rectification

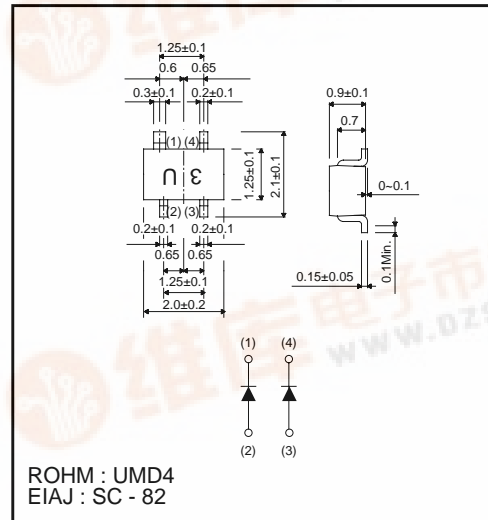
●Features

- 1) Compact size.
- 2) High reliability.
- 3) Extremely low forward voltage.
- 4) This is a composite component and is ideal for reducing the number of components used.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	30	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _o	0.2	A
Peak forward surge current*	I _{FSM}	1	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

* 60 Hz for 1

●Electrical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{F1}	-	0.18	0.28	V	I _F =1mA
	V _{F2}	-	0.25	0.33	V	I _F =10mA
	V _{F3}	-	0.34	0.43	V	I _F =100mA
	V _{F4}	-	0.40	0.50	V	I _F =200mA
Reverse current	I _R	-	3.6	30	μA	V _R =10V

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● Electrical characteristic curves (Ta=25°C)

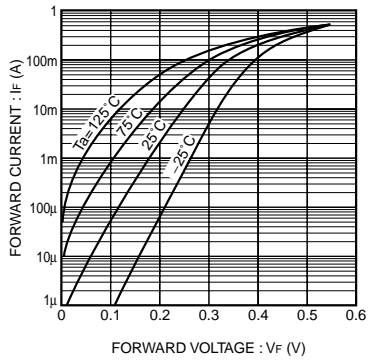


Fig. 1 Forward temperature characteristic

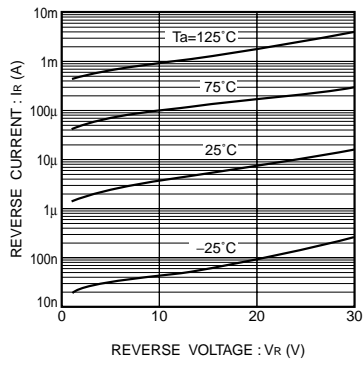


Fig. 2 Reverse temperature characteristic

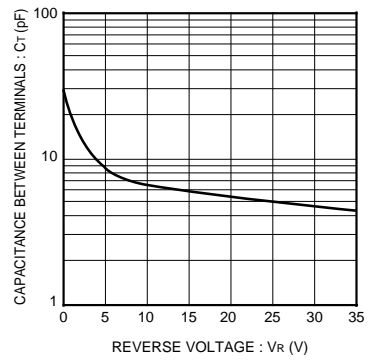


Fig. 3 Capacitance between terminals characteristic